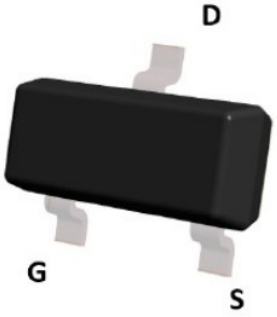
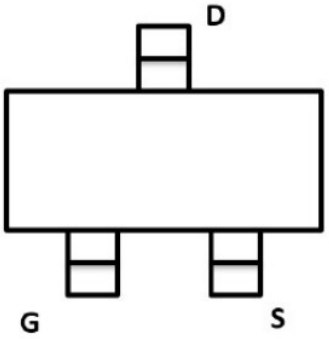
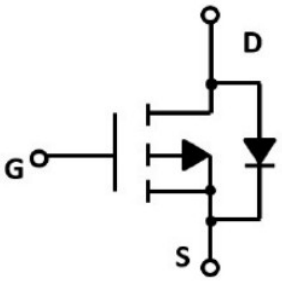
P-Channel Enhancement Mode Field Effect Transistor



Top View





SOT-23

RoHS

Product Summary

- V_{DS} -20V
- I_D -3.4A
- $R_{DS(ON)}$(at V_{GS}=-4.5V) <51mohm
- $R_{DS(ON)}$(at V_{GS}=-2.5V) <67mohm
- $R_{DS(ON)}$(at V_{GS}=-1.8V) <91mohm
- 100% ∇V_{DS} Tested

General Description

- Trench Power LV MOSFET technology
- High Power and Current handing capability
- Low Gate Charge

Applications

- PWM applications
- Power management
- Load switch

▪ Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	-20	V
Gate-source Voltage		V_{GS}	±10	V
Drain Current	T_A=25℃	I_D	-3.4	A
	T_A=70℃		-2.7	
Pulsed Drain Current [A]		I_{DM}	-14	A
Total Power Dissipation	T_A=25℃	P_D	1	W
	T_A=70℃		0.64	W
Thermal Resistance Junction-to-Ambient [B]		$R_{\theta JA}$	125	℃/ W
Junction and Storage Temperature Range		T_J ,T_{STG}	-55～+150	℃

▪ Ordering Information (Example)

PREFERED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
ELV2076RPO	F2	E76RP	3000	30000	120000	7 "reel

■ Electrical Characteristics (T_J=25℃ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=-250μA	-20			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-20V,V_{GS}=0V			-1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±10V, V_{DS}=0V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}= V_{GS}, I_D=-250μA	-0.4	-0.62	-1.0	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=-4.5V, I_D=-3.4A		42	51	mΩ
		V_{GS}=-2.5V, I_D=-3.0A		55	67	
		V_{GS}=-1.8V, I_D=-2.5A		76	91	
Diode Forward Voltage	V_{SD}	I_S=-3.4A,V_{GS}=0V			-1.2	V
Dynamic Parameters						
Input Capacitance	C_{iss}	V_{DS}=-10V,V_{GS}=0V,f=1MHZ		438		pF
Output Capacitance	C_{oss}			76		
Reverse Transfer Capacitance	C_{rss}			62		
Switching Parameters						
Total Gate Charge	Q_g	V_{GS}=-4.5V,V_{DS}=-10V,I_D=-3.4A		5.41		nC
Gate-Source Charge	Q_{gs}			1.17		
Gate-Drain Charge	Q_{gd}			1.24		
Reverse Recovery Chrage	Q_{rr}	I_F=-3.4A, di/dt=100A/us		4		
Reverse Recovery Time	t_{rr}			24.5		ns
Turn-on Delay Time	$t_{D(on)}$	V_{GS}=-4.5V, V_{DS}=-10V, I_D=-1A R_{GEN}=3Ω		6.4		
Turn-on Rise Time	t_r			21.8		
Turn-off Delay Time	$t_{D(off)}$			37.4		
Turn-off fall Time	t_f			34		

A. Pulse Test: Pulse Width≤300us,Duty cycle ≤2%.

B. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design, while $R_{\theta JA}$ is determined by the board design. The maximum rating presented here is based on mounting on a 1 in 2 pad of 2oz copper.

■ Typical Performance Characteristics

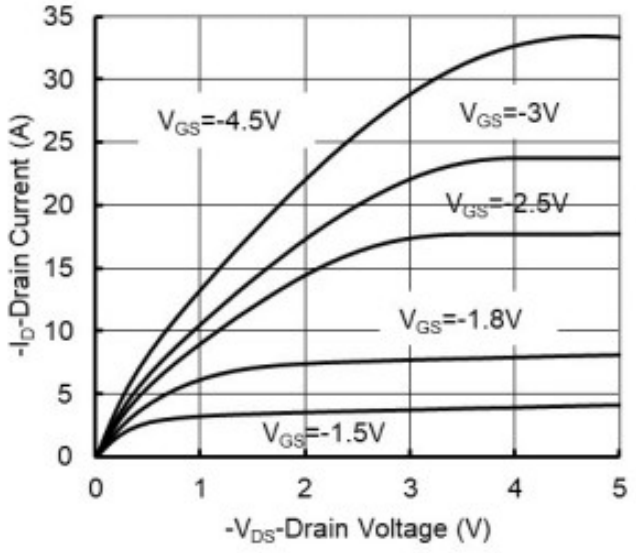


Figure1. Output Characteristics

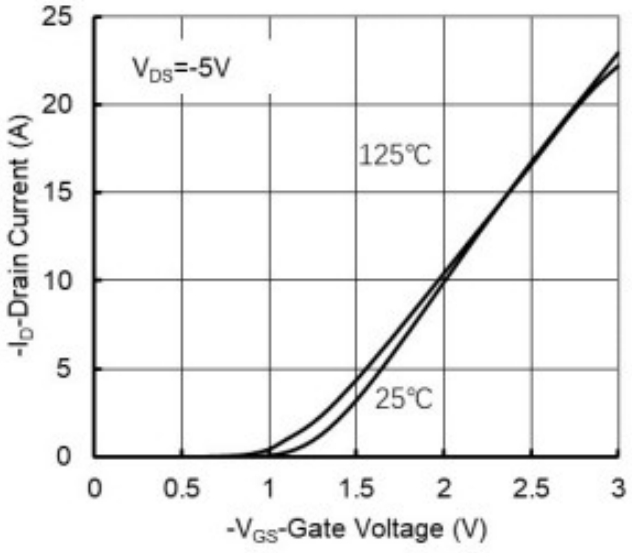


Figure2. Transfer Characteristics

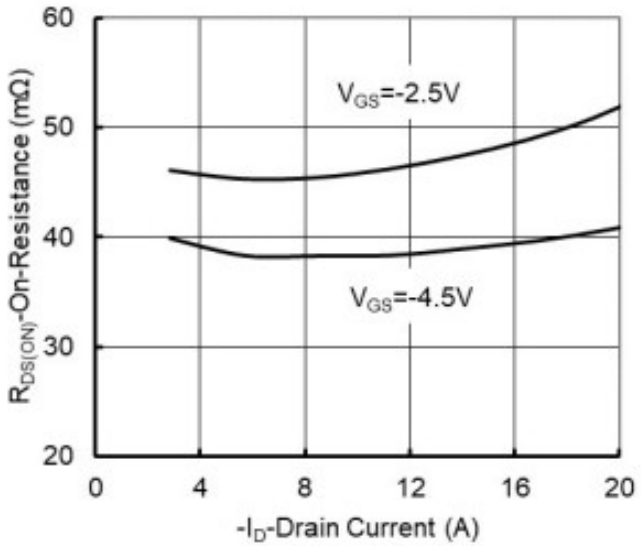


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

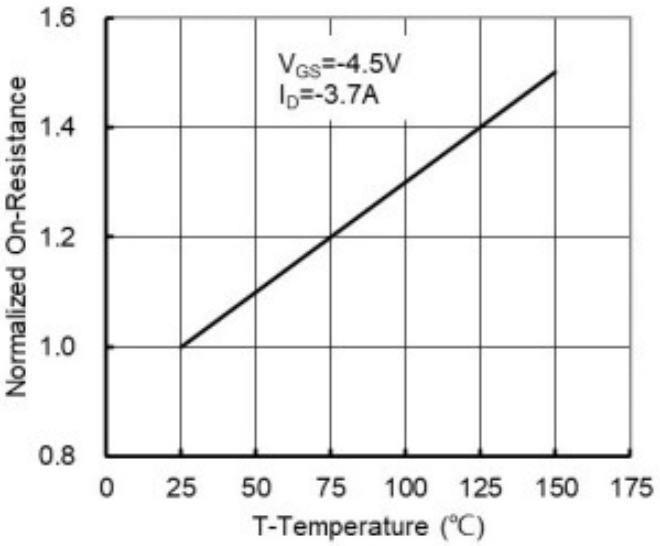


Figure 4: On-Resistance vs. Junction Temperature

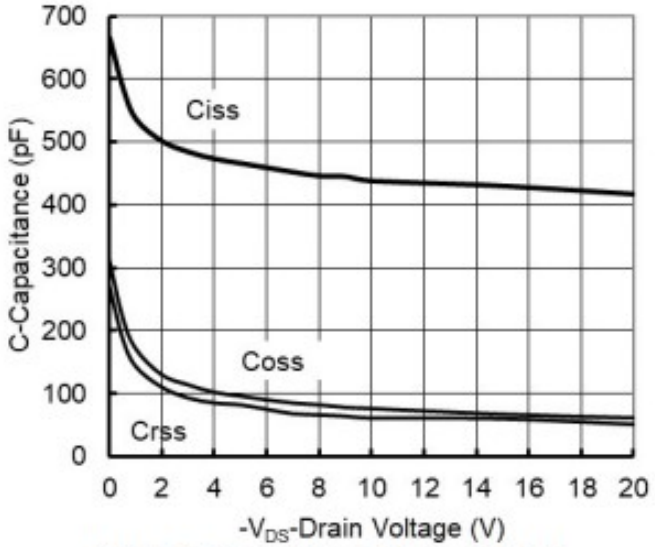


Figure5. Capacitance Characteristics

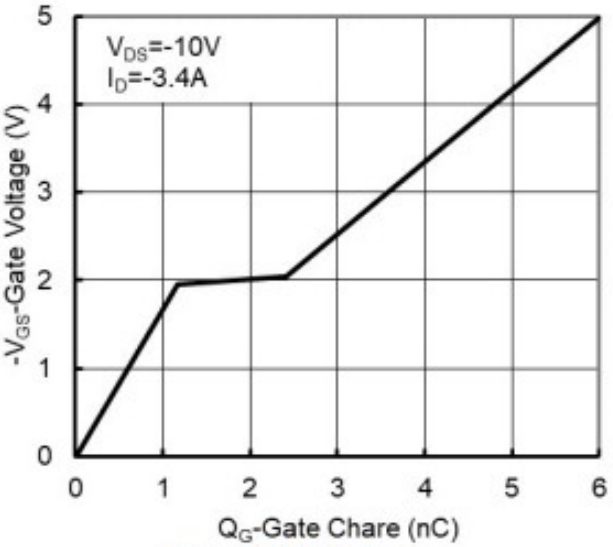


Figure6. Gate Charge

■ Typical Performance Characteristics

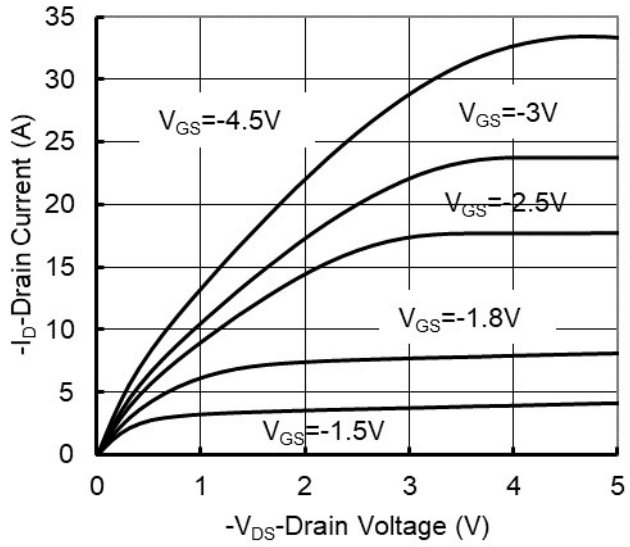


Figure1. Output Characteristics

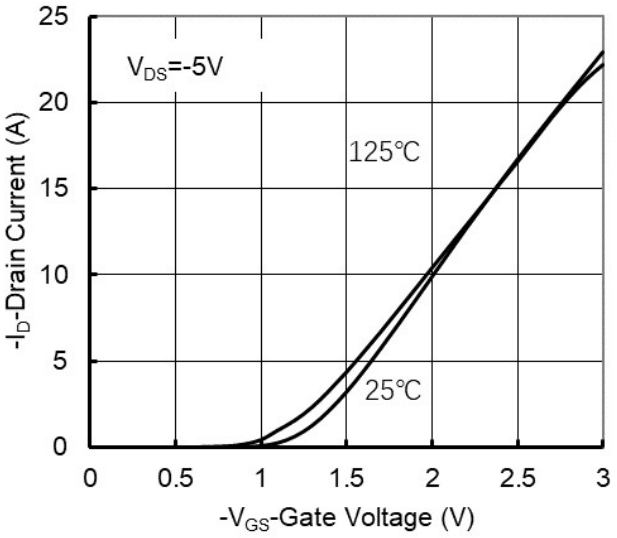


Figure2. Transfer Characteristics

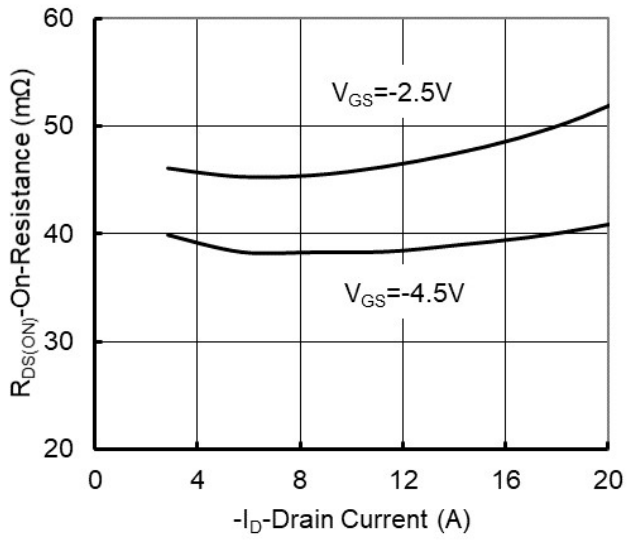


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

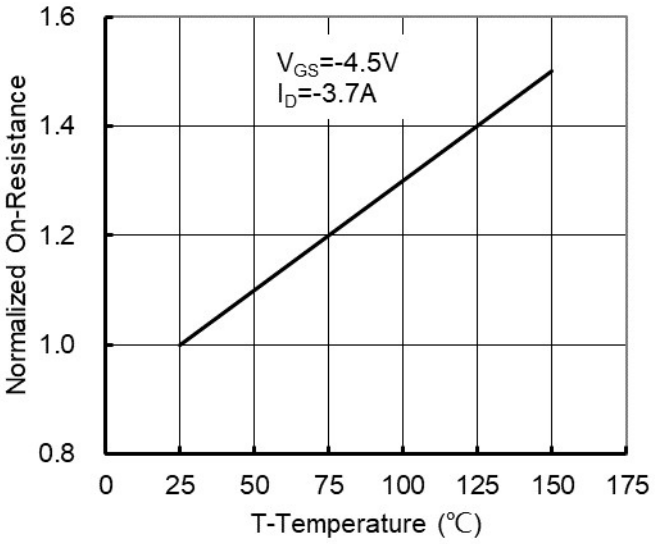


Figure 4: On-Resistance vs. Junction Temperature

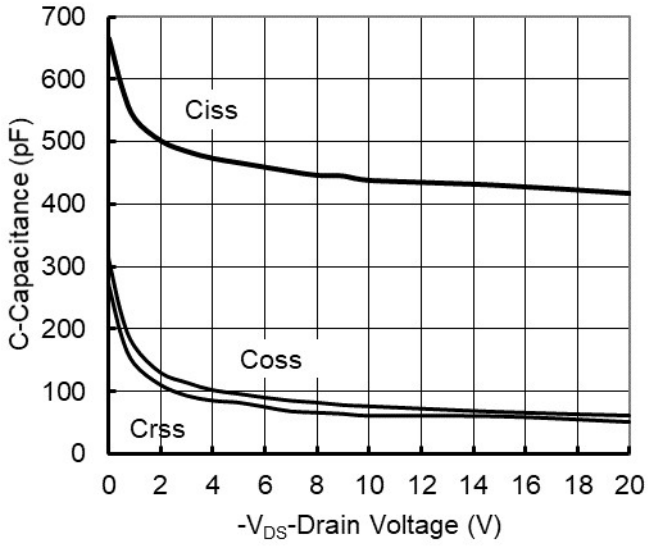


Figure5. Capacitance Characteristics

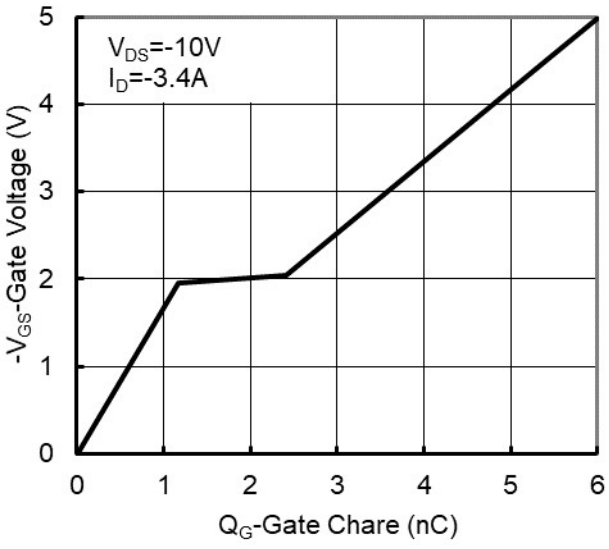


Figure6. Gate Charge

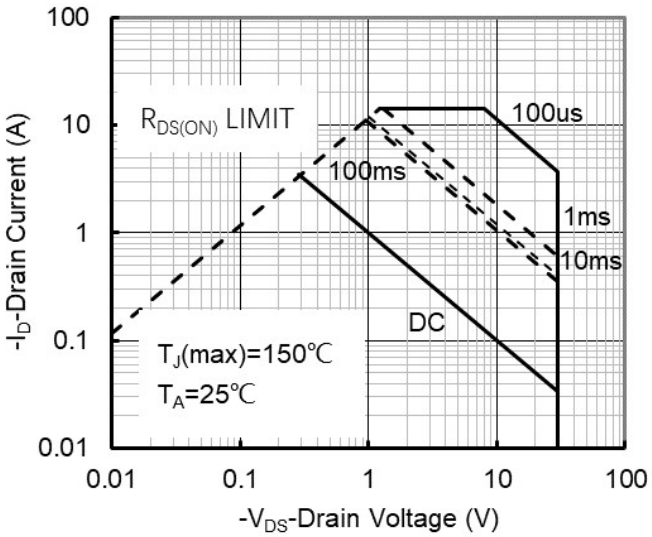


Figure7. Safe Operation Area

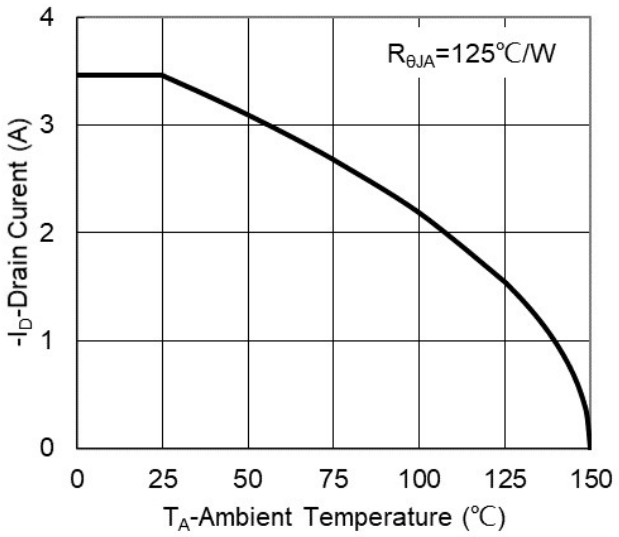


Figure8. Maximum Continuous Drain Current vs Ambient Temperature

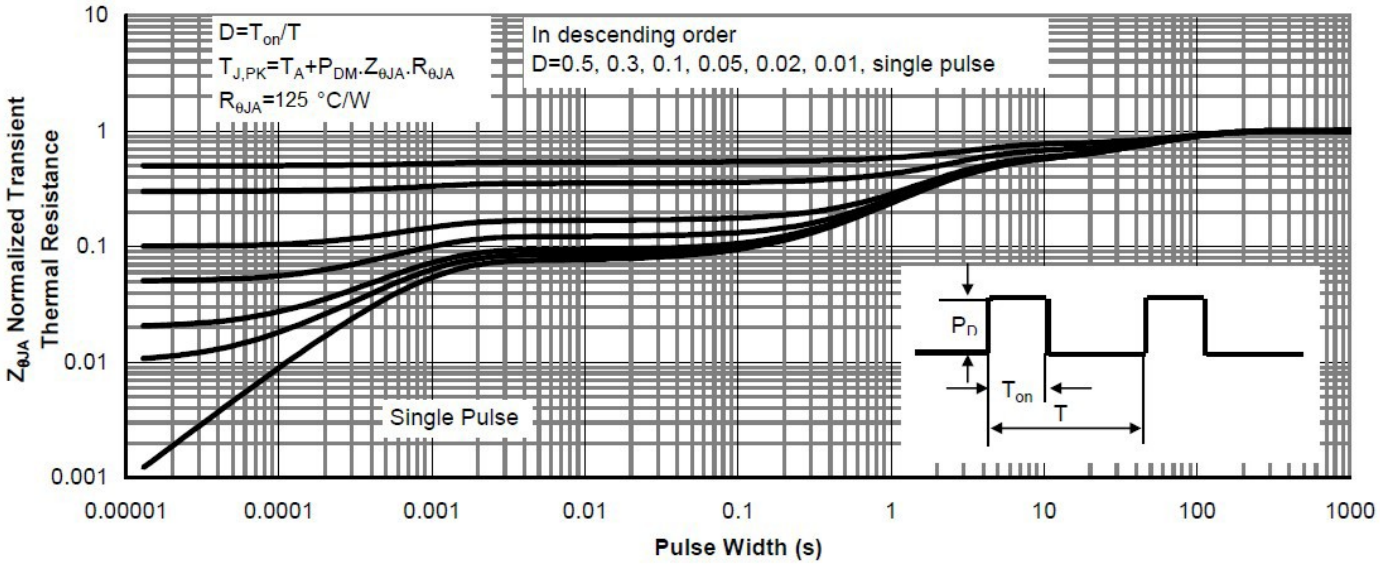
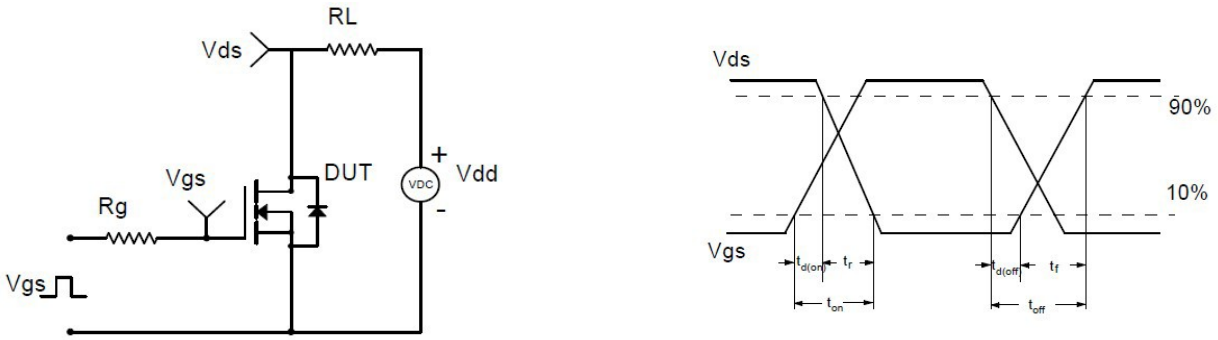
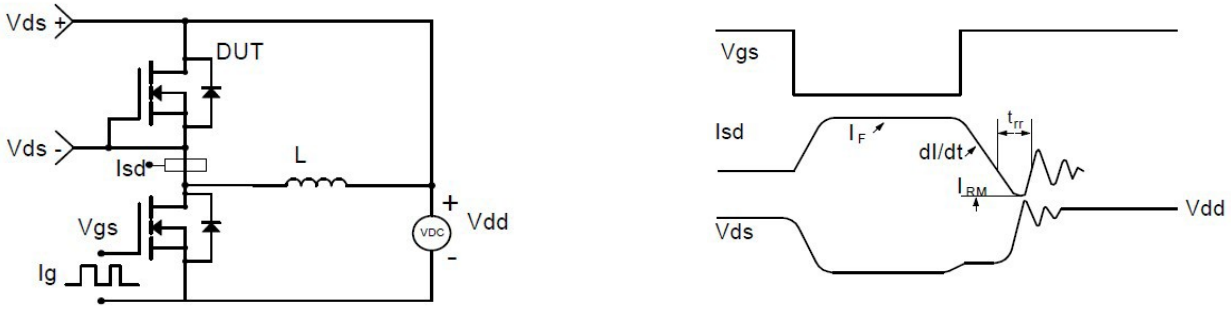


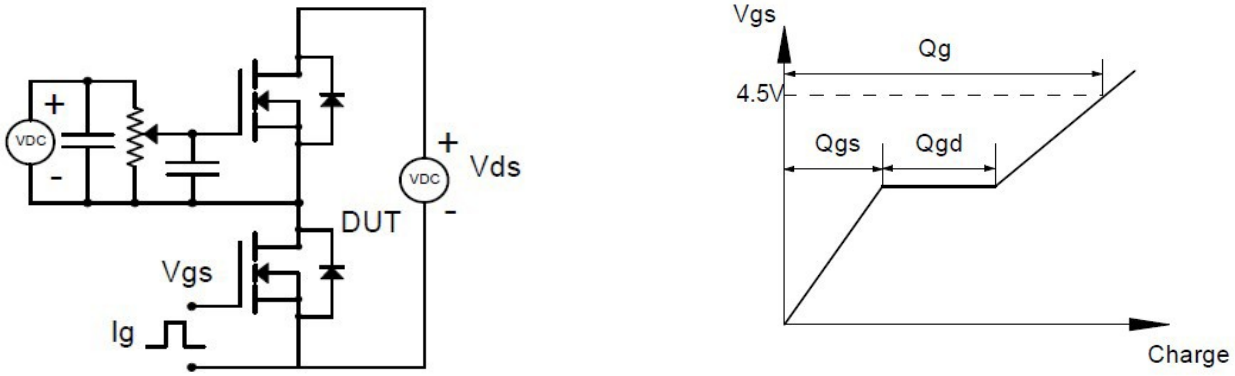
Figure9. Normalized Maximum Transient Thermal Impedance



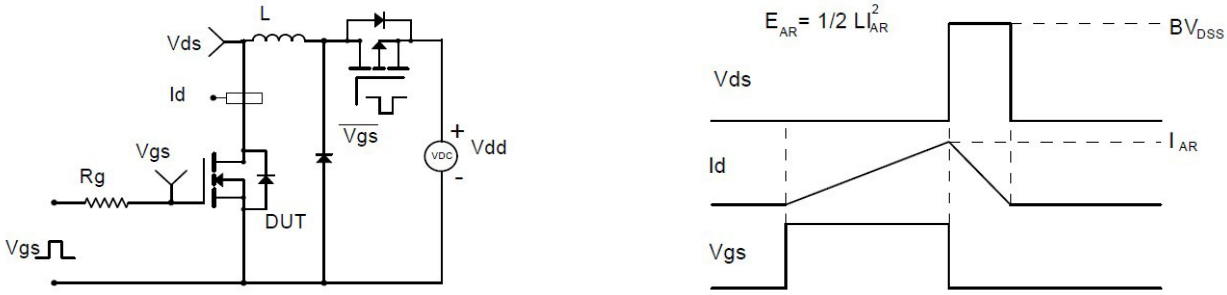
Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

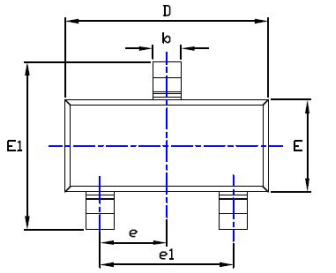


Gate Charge Test Circuit & Waveform

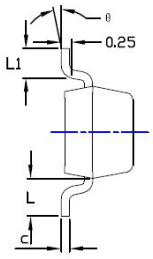


Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

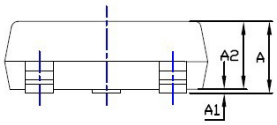
▪ SOT-23 Package information



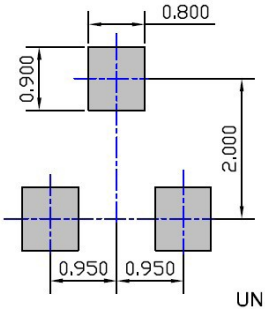
TOP VIEW



SIDE VIEW



SIDE VIEW

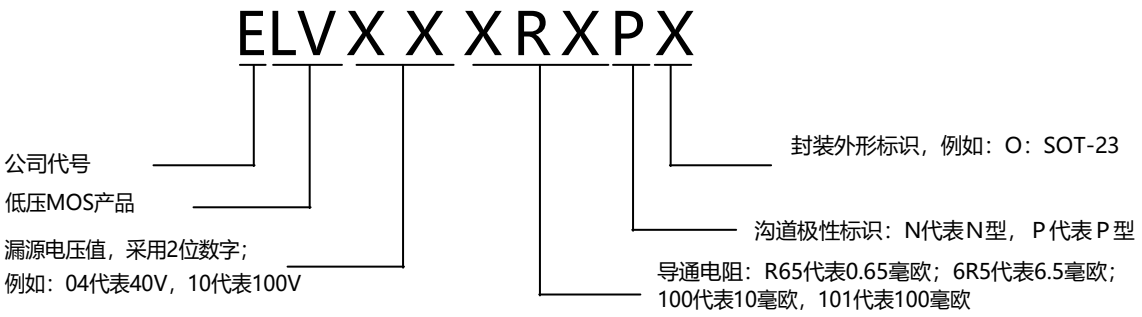


UNIT：mm

SUGGESTED SOLDER PAD LAYOUT

DIMENSIONS						
SYMBOL	INCHES			Millmeter		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.035	---	0.045	0.900	---	1.150
A1	0.000	---	0.004	0.000	---	0.100
A2	0.035	0.038	0.041	0.900	0.975	1.050
b	0.012	0.016	0.020	0.300	0.400	0.500
c	0.004	---	0.008	0.100	---	0.200
D	0.110	0.114	0.118	2.800	2.900	3.000
E	0.047	0.051	0.055	1.200	1.300	1.400
E1	0.089	0.094	0.100	2.250	2.400	2.550
e	0.037TYP			0.950TYP		
e1	0.071	0.075	0.079	1.800	1.900	2.000
L	0.022REF			0.550REF		
L1	0.012	0.016	0.200	0.300	0.400	0.500
θ	0°	---	8°	0°	---	8°

NOTE:
1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.


ELVXXXRXPX
公司代号
低压MOS产品
漏源电压值，采用2位数字；
例如：04代表40V，10代表100V
导通电阻：R65代表0.65毫欧；6R5代表6.5毫欧；
100代表10毫欧，101代表100毫欧
沟道极性标识：N代表N型， P代表P型
封装外形标识，例如：O：SOT-23